

REMARKS

Claims 1-3 were rejected as anticipated by Beneking. Claims 4-15 were rejected as unpatentable over Beneking. Applicant requests reconsideration. Independent claims were amended to recite that the MOSFET is a triode MOSFET. New claims 15 and 16 recite that the gate curvature is less than or equal to a quartercircle.

Applicant extends appreciation for the thorough examination and particularly for the recitation of Beneking. Beneking discloses pentrode MOSFETs having five electrodes, consisting of a source, two drains, and two gate electrodes, whereas, all of the present claims are now more particularly directed to triode MOSFETs consisting of a source, a drain, and a gate. As is apparent from Beneking, the pentrode MOSFETs are basically circular in configuration has opposing drains between which are disposed respective gate electrodes.

The background of the present specification recites the prior art circular designs of the triode configurations that lack an ability to pack the MOSFETs in silicon for high density integration, while also disclosing the prior art semicircular serpentine configurations. By contradistinction, the present invention enables high-density integration of MOSFETs similar to a stack of shallow bowls, and hence, the particular $1/4$ and $1/8$ circular designs of the preferred embodiments. Beneking teaches the OLD prior art circular type design that does not address the poor packing density problem. While Beneking does show gates that are curved and slightly less a semicircle, that difference was slight

1 to accommodate two separate gates with opposing respective drains,
2 but in total is still a circular design. The new claims recite a
3 limitation of a quartercircle or less curvature that allows for
4 efficient packing integration of large numbers of MOSFETs while
5 retraining the curved gate structure, not taught by Beneking. All
6 of the claims have now been limited to only triode MOSFETS, and
7 hence, are not anticipated Beneking. Beneking directly teaches away
8 from a triode configuration and does not address the problem of
9 poor packing density of integrated MOSFETS, which problem is solved
10 by the present invention, having curved gates in a triode
11 configuration, and hence, Beneking does not render the present
12 claims unpatentable. Allowance of the claims is kindly requested.

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16 Respectfully Submitted

17 *Derrick Michael Reid*

18 Derrick Michael Reid

19 Derrick Michael Reid, Esq.

20 The Aerospace Corporation

21 PO Box 92957 M1/040

22 Los Angeles, Ca 90009-2957

23 Reg. No. 32,096

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